

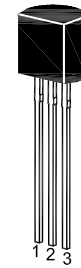
2SC3279

NPN Silicon Epitaxial Planar Transistor

for storobo flash and medium power amplifier applications.

The transistor is subdivided into four groups L, M, N and P, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



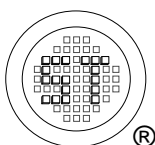
1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	30	V
Collector Emitter Voltage	V_{CES}	30	V
Collector Emitter Voltage	V_{CEO}	10	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current (DC)	I_C	2	A
Collector Current (Pulse Width = 10 ms)	I_{CP}	5	A
Base Current	I_B	0.2	A
Power Dissipation	P_{tot}	750	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE} = 1\text{ V}$, $I_C = 500\text{ mA}$ at $V_{CE} = 1\text{ V}$, $I_C = 2\text{ A}$ Current Gain Group	L	h_{FE}	140	-	240	-
	M	h_{FE}	200	-	330	-
	N	h_{FE}	300	-	450	-
	P	h_{FE}	420	-	600	-
			h_{FE}	70	200	-
Collector Base Cutoff Current at $V_{CB} = 30\text{ V}$	I_{CBO}	-	-	0.1	μA	
Emitter Base Cutoff Current at $V_{EB} = 6\text{ V}$	I_{EBO}	-	-	0.1	μA	
Collector-Emitter Breakdown Voltage at $I_C = 10\text{ mA}$	$V_{(BR)CEO}$	10	-	-	V	
Emitter Base Breakdown Voltage at $I_E = 1\text{ mA}$	$V_{(BR)EBO}$	6	-	-	V	
Collector Emitter Saturation Voltage at $I_C = 2\text{ A}$, $I_B = 50\text{ mA}$	$V_{CE(sat)}$	-	0.2	0.5	V	
Base Emitter Voltage at $V_{CE} = 1\text{ V}$, $I_C = 2\text{ A}$	V_{BE}	-	0.86	1.5	V	
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	27	-	pF	
Transition Frequency at $V_{CE} = 1\text{ V}$, $I_C = 0.5\text{ A}$	f_T	-	150	-	MHz	



SEMTECH ELECTRONICS LTD.



ISO/TS 16949 : 2009 Certificate No. 180713000
 ISO14001 : 2004 Certificate No. 7116
 ISO 9001 : 2008 Certificate No. 50712410
 BS-OHSAS 18001 : 2007 Certificate No. 7116
 IECQ QC 080000 Certificate No. PFC:SPM-1483-1

Dated : 20/01/2016 CL Rev: 01

